



Surface Mount Transistors

Saturated Switches—PNP

Type No.	Case Style	V _{CE} [*] V _{CE0} (V) Min	V _{BE} (V) Min	I _{CE} [*] I _{CE0} (nA) Max	V _{CE} @ I _C & V _{BE} (V) Min Max	I _C @ V _{BE} (SAT) (mA) Min Max (I _B = 10 ⁻¹)	C _{ob} (pF) Max	f _r (MHz) Min Max	t _{off} (ns) Max	Test Conditions	Process No.
MMBT 3639	TO-236 (49)	6	4	50*	30 120 10 0.3 20 50 1	0.16 0.5 0.2 0.6	5.5	300 10	60	(Note 7)	65
MMBT 3640	TO-236 (49)	12	4	50*	30 120 10 0.3 20 50 1	0.15 0.5 0.2 0.6	5.5	300 10	75	(Note 7)	65
MMBT 4258	TO-236 (49)	12	4.5	10*	30 120 10 0.3 15 1 0.5 30 50 1	0.15 0.75 0.95 0.5 1.5	3	500 10	20	(Note 6)	65
MMBT 5228	TO-236 (49)	5	3	100*	30 10 3 30 10 3	0.4 0.65 1.25 0.4 0.65 1.25	5	300 10			65
MMBT 5771	TO-236 (49)	15	4.5	10	50 120 10 0.3 40 50 1 35 1 0.3	0.15 0.8 0.18 0.8 0.95 0.6 1.5	3	700 10	20	(Note 6)	65
MMBT 5771-1	TO-236 (49)	15	4.5	10	30 150 10 0.3 20 50 1 30 1 0.5	0.15 0.8 0.18 0.8 0.95 0.6 1.5	3	700 10	30	(Note 6)	65
MMBT 5571-2	TO-236 (49)	15	4.5	10	40 150 10 0.3 30 50 1 35 1 0.5	0.15 0.8 0.18 0.8 0.95 0.6 1.5	3	700 10	30	(Note 6)	65
MMBT 5910	TO-236 (49)	20	4.5	10*	30 120 10 0.3 15 1 0.5	0.15 0.75 0.95 0.5 1.5	3	700 10	20	(Note 6)	65

TEST CONDITIONS:

Note 1: V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1.5 mA
 Note 2: V_{CC} = 3V, I_C = 10 mA, I_B¹ = 3 mA, I_B² = 1 mA
 Note 3: V_{CC} = 10V, I_C = 300 mA, I_B¹ = I_B² = 30 mA
 Note 4: V_{CC} = 2V, I_C = 30 mA, I_B¹ = I_B² = 3 mA

Note 5: V_{CC} = 25V, I_C = 300 mA, I_B¹ = I_B² = 30 mA
 Note 6: V_{CC} = 25V, I_C = 600 mA, I_B¹ = I_B² = 50 mA
 Note 7: V_{CC} = 30V, I_C = 500 mA, I_B¹ = I_B² = 50 mA
 Note 8: V_{CC} = 30V, I_C = 1A, I_B¹ = I_B² = 100 mA

Note 9: V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 1 mA
 Note 10: V_{CC} = 10.7V, I_C = 1A, I_B¹ = I_B² = 100 mA
 Note 11: V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3 mA
 Note 12: V_{CC} = 3V, I_C = 10 mA, I_B¹ = I_B² = 3.3 mA

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